

SANYO Semiconductors DATA SHEET

2SC4161—NPN Triple Diffused Planar Silicon Transistor Switching Regulator Applications

Features

- · High breakdown voltage, high reliability.
- High-speed switching (tf: 0.1µs typ).
- · Wide ASO.
- · Adoption of MBIT process.
- · Micaless package facilitating mounting.

Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	V _{CBO}		500	V
Collector-to-Emitter Voltage	VCEO		400	V
Emitter-to-Base Voltage	VEBO		7	V
Collector Current	IC		7	Α
Collector Current (Pulse)	ICP	PW≤300μs, duty cycle≤10%	14	Α
Base Current	IΒ		3	Α
Collector Dissipation	D-		2	W
	PC	Tc=25°C	30	W
Junction Temperature	Tj		150	°C
Storage Temperature	Tstg		-55 to +150	°C

Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
		Conditions	min	typ	max	Onne
Collector Cutoff Current	ІСВО	VCB=400V, IE=0A			10	μΑ
Emitter Cutoff Current	IEBO	V _{EB} =5V, I _C =0A			10	μΑ

Continued on next page.

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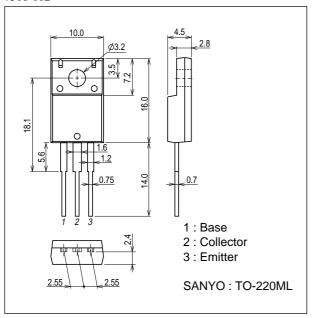
Parameter	Symbol Conditions	Conditions	Ratings			Unit
		min	typ	max) Offic	
	hFE1	VCE=5V, IC=0.8A	15*		50*	
DC Current Gain	hFE2	V _{CE} =5V, I _C =4A	10			
	hFE3	VCE=5V, IC=10mA	10			
Gain-Bandwidth Product	fT	V _{CE} =10V, I _C =0.8A		20		MHz
Output Capacitance	Cob	V _{CB} =10V, f=1MHz		80		pF
Collector-to-Emitter Saturation Voltage	VCE(sat)	IC=4A, IB=0.8A			0.8	V
Base-to-Emitter Saturation Voltage	V _{BE} (sat)	I _C =4A, I _B =0.8A			1.5	V
Collector-to-Base Breakdown Voltage	V(BR)CBO	I _C =1mA, I _E =0A	500			V
Collector-to-Emitter Breakdown Voltage	V(BR)CEO	IC=5mA, RBE=∞	400			V
Emitter-to-Base Breakdown Voltage	V(BR)EBO	IE=1mA, IC=0A	7			V
Collector-to-Emitter Sustain Voltage	VCEX(sus)	I _C =3A, I _{B1} =0.3A, I _{B2} =-1.2A, L=1mH, Clamped	400			V
Turn-ON Time	ton	IC=5A, IB1=1A, IB2=-2A, RL=40Ω, VCC=200V			0.5	μS
Storage Time	tstg	I _C =5A, I _{B1} =1A, I _{B2} =-2A, R _L =40Ω, V _{CC} =200V			2.5	μS
Fall Time	tf	I _C =5A, I _{B1} =1A, I _{B2} =-2A, R _L =40Ω, V _{CC} =200V			0.3	μS

*: The hFE1 of the 2SC4161 is classified as follows. When specifying the hFE1 rank, specify two ranks or more in principle.

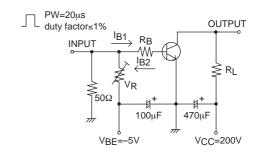
Rank	L	M	N		
hFE	15 to 30	20 to 40	30 to 50		

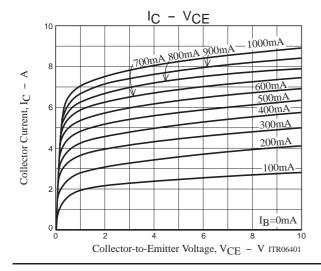
Package Dimensions

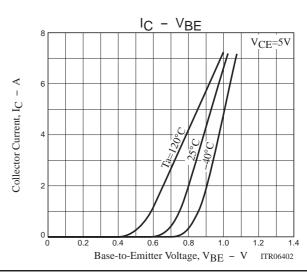
unit : mm (typ) 7508-002

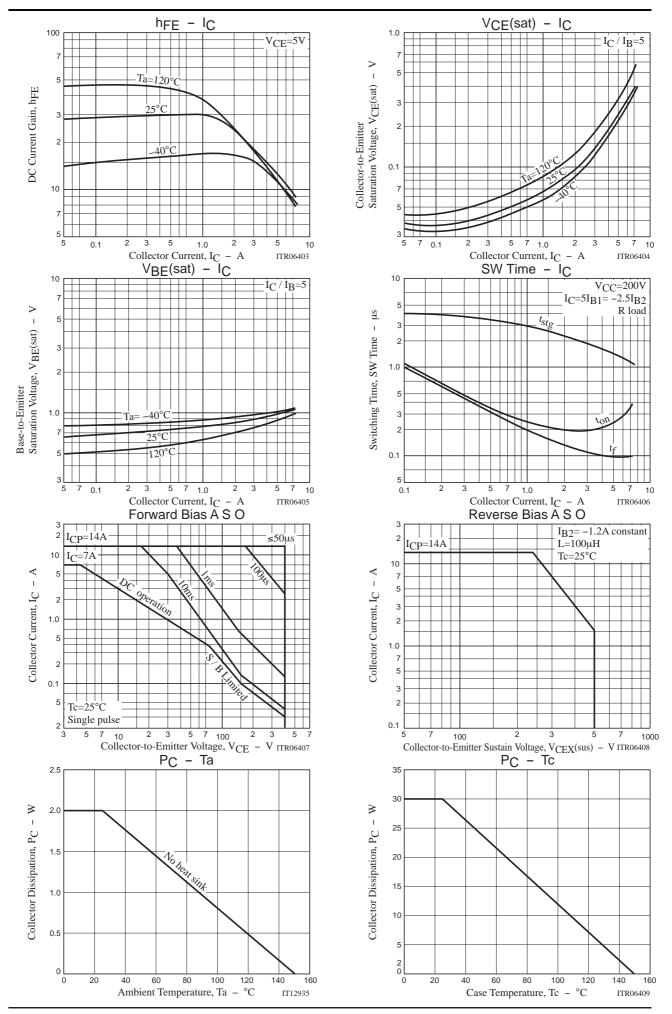


Switching Time Test Circuit









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